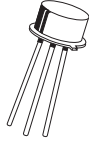


BSX62
BSX63

NPN SILICON TRANSISTOR



TO-39 CASE

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR BSX62, BSX63 types are NPN Silicon Transistors designed for general purpose applications where high collector current is required.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_C=25^\circ\text{C}$)

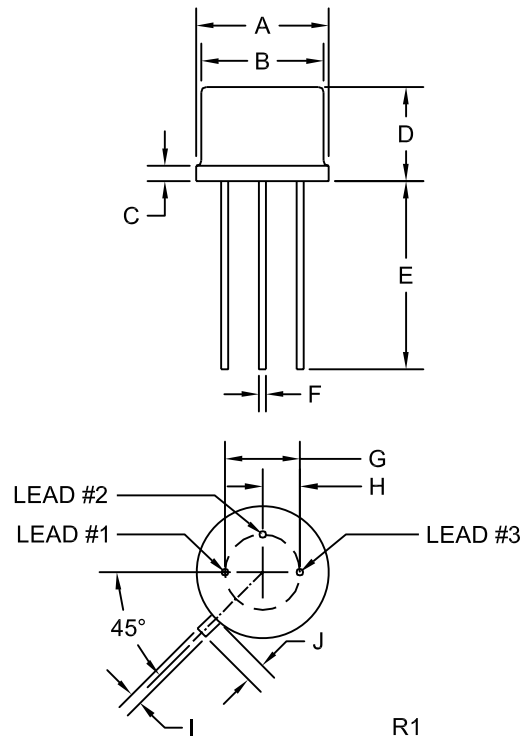
	SYMBOL	BSX62	BSX63	UNITS
Collector-Base Voltage	V_{CBO}	60	80	V
Collector-Emitter Voltage	V_{CEO}	40	60	V
Emitter-Base Voltage	V_{EBO}	5.0		V
Collector Current	I_C	3.0		A
Power Dissipation	P_D	5.0		W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +200		$^\circ\text{C}$
Thermal Resistance	θ_{JC}	35		$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{CBO}	$V_{CB}=40\text{V}$ (BSX62)			100	nA
I_{CBO}	$V_{CB}=40\text{V}$, $T_C=150^\circ\text{C}$ (BSX62)			100	μA
I_{CBO}	$V_{CB}=60\text{V}$ (BSX63)			100	nA
I_{CBO}	$V_{CB}=60\text{V}$, $T_C=150^\circ\text{C}$ (BSX63)			100	μA
I_{EBO}	$V_{EB}=5.0\text{V}$			100	nA
$V_{CE(SAT)}$	$I_C=1.0\text{A}$, $I_B=100\text{mA}$			0.7	V
$V_{CE(SAT)}$	$I_C=2.0\text{A}$, $I_B=200\text{mA}$			0.8	V
$V_{BE(SAT)}$	$I_C=1.0\text{A}$, $I_B=100\text{mA}$			1.2	V
$V_{BE(SAT)}$	$I_C=2.0\text{A}$, $I_B=200\text{mA}$			1.3	V
$V_{BE(ON)}$	$V_{CE}=1.0\text{V}$, $I_C=100\text{mA}$			1.0	V
$V_{BE(ON)}$	$V_{CE}=1.0\text{V}$, $I_C=1.0\text{A}$			1.2	V
$V_{BE(ON)}$	$V_{CE}=5.0\text{V}$, $I_C=2.0\text{A}$			1.3	V
h_{FE}	$V_{CE}=1.0\text{V}$, $I_C=1.0\text{A}$ (BSX62, 63-10)	63		160	
h_{FE}	$V_{CE}=1.0\text{V}$, $I_C=1.0\text{A}$ (BSX62, 63-16)	100		250	
C_{ob}	$V_{CB}=10\text{V}$, $I_E=0$, $f=1.0\text{MHz}$			70	pF
f_T	$V_{CE}=10\text{V}$, $I_C=200\text{mA}$, $f=100\text{MHz}$	30			MHz
t_{on}	$I_C=1.0\text{A}$, $I_{B1}=I_{B2}=50\text{mA}$			300	ns
t_{off}	$I_C=1.0\text{A}$, $I_{B1}=I_{B2}=50\text{mA}$		4.0		μs

R0 (2-April 2008)

TO-39 CASE - MECHANICAL OUTLINE



DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.335	0.370	8.51	9.40
B (DIA)	0.315	0.335	8.00	8.51
C	-	0.040	-	1.02
D	0.240	0.260	6.10	6.60
E	0.500	-	12.70	-
F (DIA)	0.016	0.021	0.41	0.53
G (DIA)	0.200		5.08	
H	0.100		2.54	
I	0.028	0.034	0.71	0.86
J	0.029	0.045	0.74	1.14

TO-39 (REV: R1)

LEAD CODE:

- 1) EMITTER
- 2) BASE
- 3) COLLECTOR (case)

MARKING: FULL PART NUMBER

R0 (2-April 2008)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

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